

# General Purpose Transistors

## NPN Silicon

# MMBT2222L, MMBT2222AL, SMMBT2222AL

### Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

### MAXIMUM RATINGS

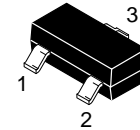
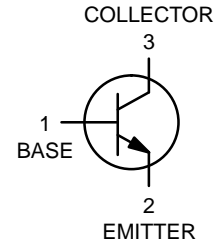
Rating	Symbol	Value	Unit
Collector-Emitter Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	$V_{CEO}$	30 40	Vdc
Collector-Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	$V_{CBO}$	60 75	Vdc
Emitter-Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	$V_{EBO}$	5.0 6.0	Vdc
Collector Current - Continuous	$I_C$	600	mAdc
Collector Current - Peak (Note 3)	$I_{CM}$	1100	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

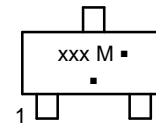
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.
3. Reference SOA curve.



SOT-23  
CASE 318  
STYLE 6

### MARKING DIAGRAM



xxx = 1P or M1B  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

# MMBT2222L, MMBT2222AL, SMMBT2222AL

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	MMBT2222 MMBT2222A	V <sub>(BR)CEO</sub>	30 40	– –	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	MMBT2222 MMBT2222A	V <sub>(BR)CBO</sub>	60 75	– –	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	MMBT2222 MMBT2222A	V <sub>(BR)EBO</sub>	5.0 6.0	– –	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB(off)</sub> = 3.0 Vdc)	MMBT2222A, SMMBT2222A	I <sub>CEX</sub>	–	10	nAdc
Collector Cutoff Current (V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0)	MMBT2222 MMBT2222A, SMMBT2222A	I <sub>CBO</sub>	–	0.01	μAdc
(V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0)	MMBT2222A, SMMBT2222A		–	0.01	
(V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 125°C)	MMBT2222		–	10	
(V <sub>CB</sub> = 60 Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 125°C)	MMBT2222A, SMMBT2222A		–	10	
Emitter Cutoff Current (V <sub>EB</sub> = 3.0 Vdc, I <sub>C</sub> = 0)	MMBT2222A, SMMBT2222A	I <sub>EBO</sub>	–	100	nAdc
Base Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB(off)</sub> = 3.0 Vdc)	MMBT2222A, SMMBT2222A	I <sub>BL</sub>	–	20	nAdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain (I <sub>C</sub> = 0.1 mAdc, V <sub>CE</sub> = 10 Vdc) (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc, T <sub>A</sub> = –55°C) (I <sub>C</sub> = 150 mAdc, V <sub>CE</sub> = 10 Vdc) (Note 4) (I <sub>C</sub> = 150 mAdc, V <sub>CE</sub> = 1.0 Vdc) (Note 4) (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc) (Note 4)	MMBT2222A only      MMBT2222 MMBT2222A, SMMBT2222A	h <sub>FE</sub>	35 50 75 35 100 50 30 40	– – – – 300 – – –	–
Collector–Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc)	MMBT2222 MMBT2222A, SMMBT2222A	V <sub>CE(sat)</sub>	– –	0.4 0.3	Vdc
(I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc)	MMBT2222 MMBT2222A, SMMBT2222A		– –	1.6 1.0	
Base–Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc)	MMBT2222 MMBT2222A, SMMBT2222A	V <sub>BE(sat)</sub>	– 0.6	1.3 1.2	Vdc
(I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc)	MMBT2222 MMBT2222A, SMMBT2222A		– –	2.6 2.0	
<b>SMALL–SIGNAL CHARACTERISTICS</b>					
Current–Gain – Bandwidth Product (Note 5) (I <sub>C</sub> = 20 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)	MMBT2222 MMBT2222A, SMMBT2222A	f <sub>T</sub>	250 300	– –	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	–	8.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	MMBT2222 MMBT2222A, SMMBT2222A	C <sub>ibo</sub>	– –	30 25	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h <sub>ie</sub>	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h <sub>re</sub>	– –	8.0 4.0	X 10 <sup>–4</sup>
Small–Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h <sub>fe</sub>	50 75	300 375	–

# MMBT2222L, MMBT2222AL, SMMBT2222AL

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Output Admittance ( $I_C = 1.0\text{ mA dc}$ , $V_{CE} = 10\text{ V dc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mA dc}$ , $V_{CE} = 10\text{ V dc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	5.0 25	35 200	$\mu\text{mhos}$
Collector Base Time Constant ( $I_E = 20\text{ mA dc}$ , $V_{CB} = 20\text{ V dc}$ , $f = 31.8\text{ MHz}$ )	$r_b, C_c$	-	150	ps
Noise Figure ( $I_C = 100\ \mu\text{A dc}$ , $V_{CE} = 10\text{ V dc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF	-	4.0	dB

## SWITCHING CHARACTERISTICS (MMBT2222A only)

Delay Time	$(V_{CC} = 30\text{ V dc}$ , $V_{BE(\text{off})} = -0.5\text{ V dc}$ , $I_C = 150\text{ mA dc}$ , $I_{B1} = 15\text{ mA dc}$ )	$t_d$	-	10	ns
Rise Time		$t_r$	-	25	
Storage Time	$(V_{CC} = 30\text{ V dc}$ , $I_C = 150\text{ mA dc}$ , $I_{B1} = I_{B2} = 15\text{ mA dc}$ )	$t_s$	-	225	ns
Fall Time		$t_f$	-	60	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .
- $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

## SWITCHING TIME EQUIVALENT TEST CIRCUITS

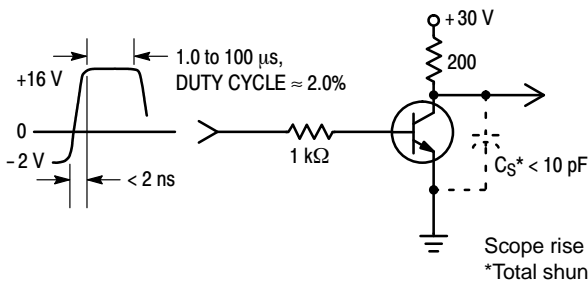


Figure 1. Turn-On Time

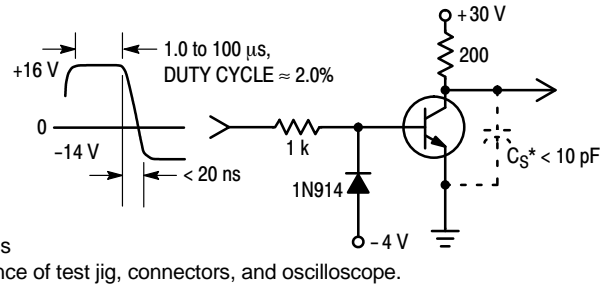


Figure 2. Turn-Off Time

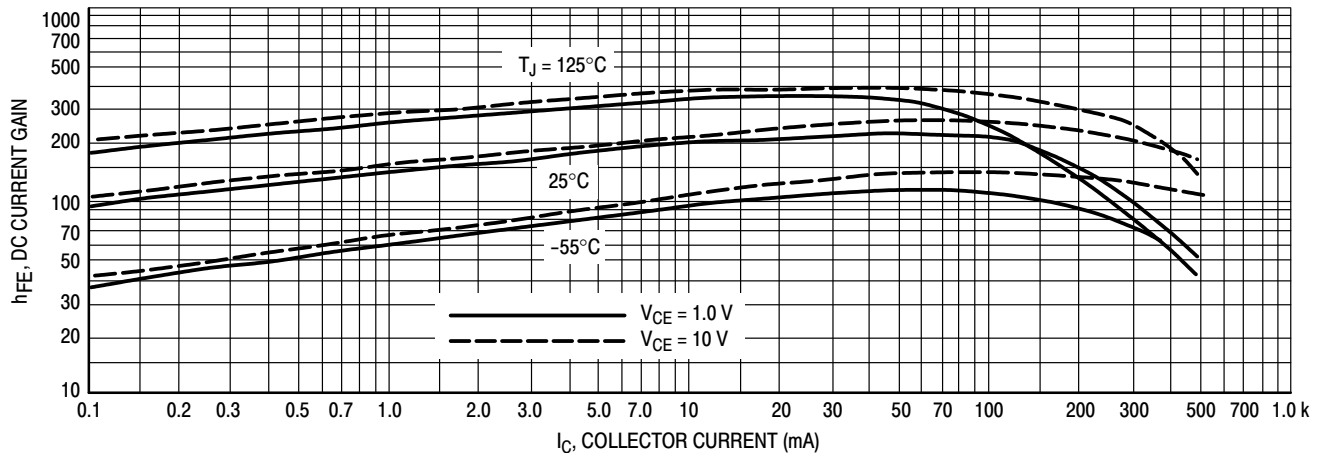


Figure 3. DC Current Gain

# MMBT2222L, MMBT2222AL, SMMBT2222AL

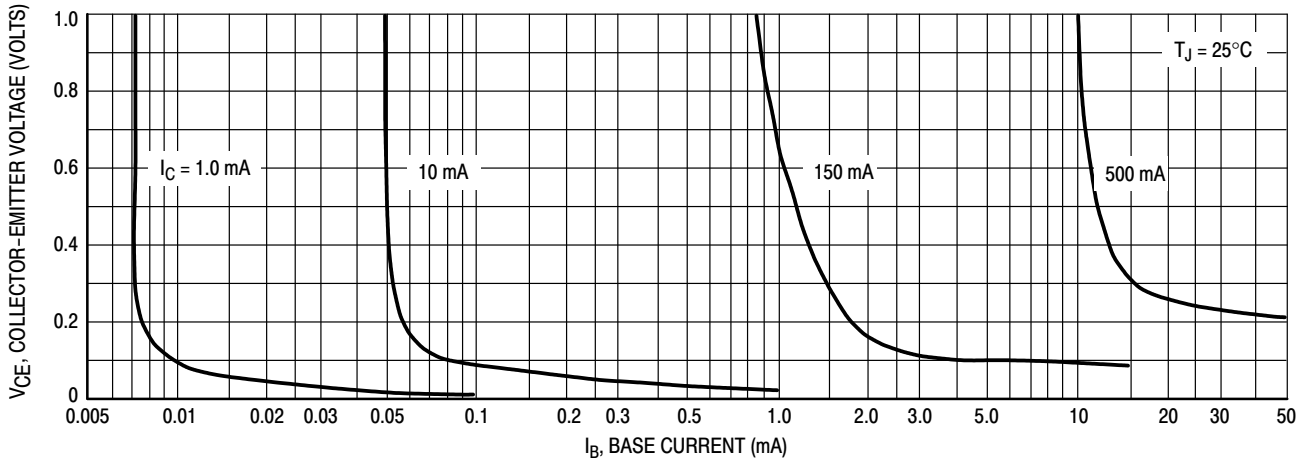


Figure 4. Collector Saturation Region

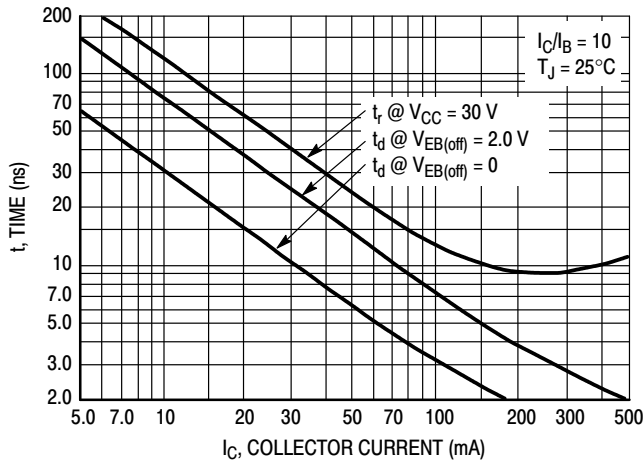


Figure 5. Turn-On Time

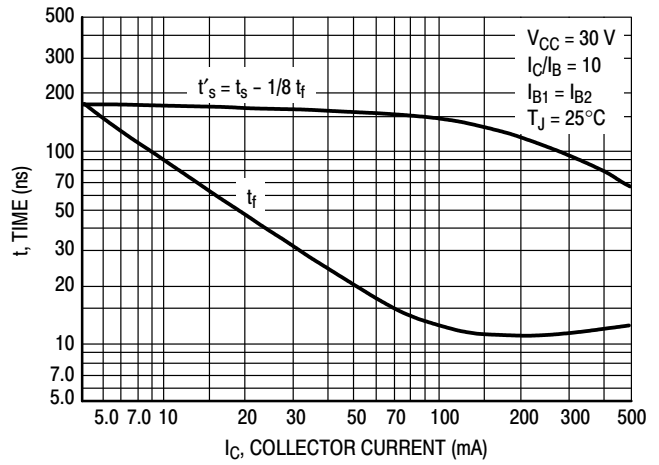


Figure 6. Turn-Off Time

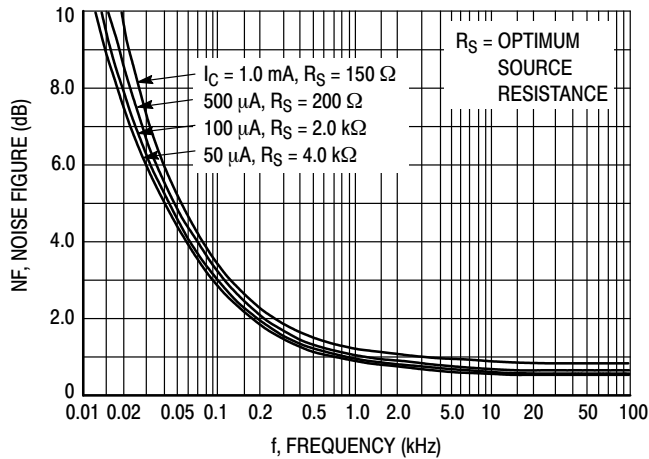


Figure 7. Frequency Effects

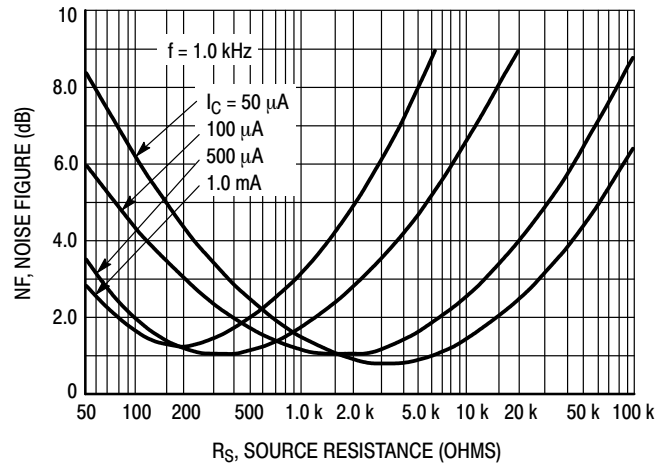


Figure 8. Source Resistance Effects

# MMBT2222L, MMBT2222AL, SMMBT2222AL

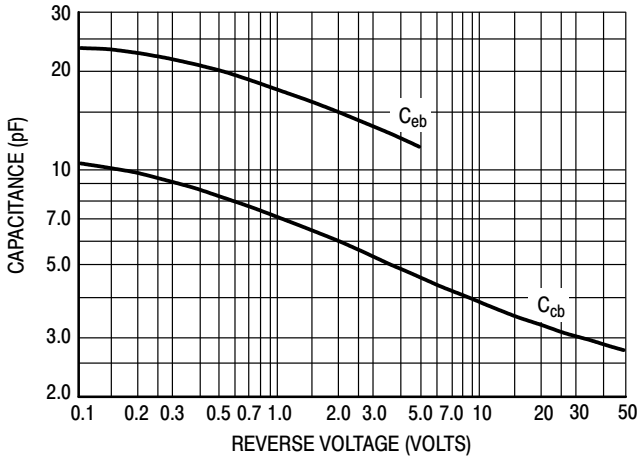


Figure 9. Capacitances

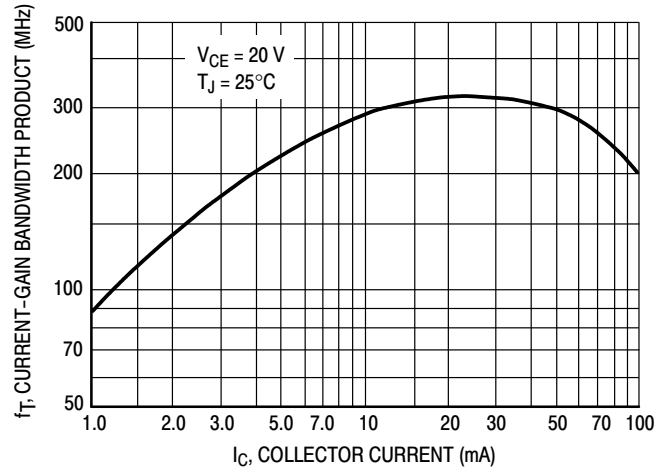


Figure 10. Current-Gain Bandwidth Product

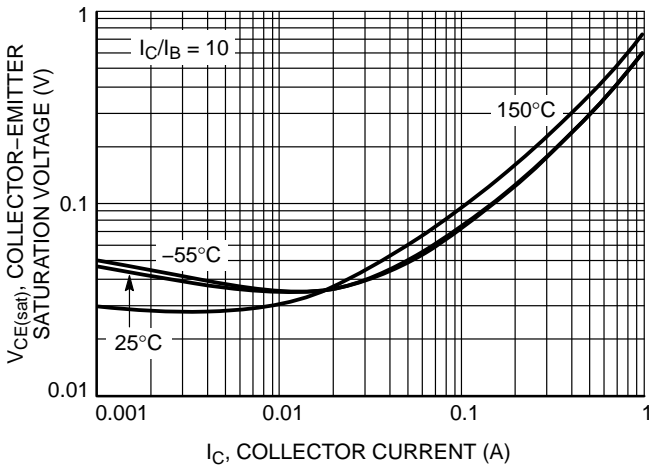


Figure 11. Collector-Emitter Saturation Voltage vs. Collector Current

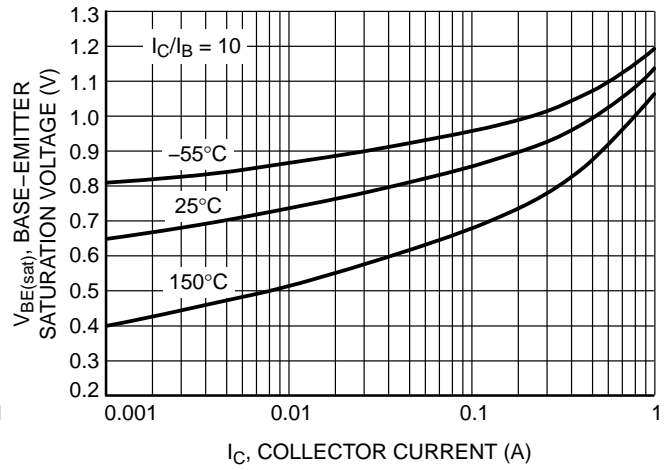


Figure 12. Base-Emitter Saturation Voltage vs. Collector Current

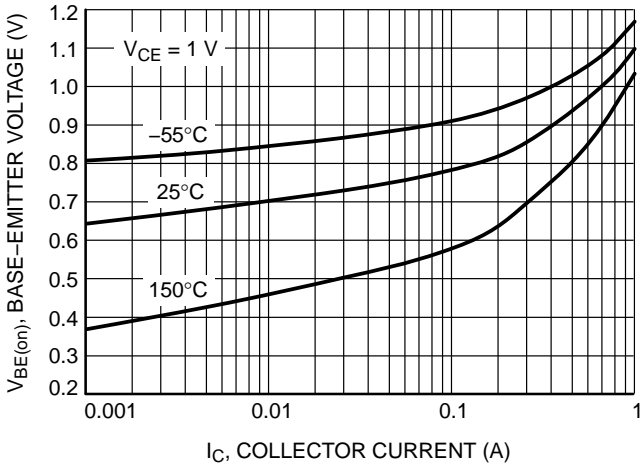


Figure 13. Base-Emitter Voltage vs. Collector Current

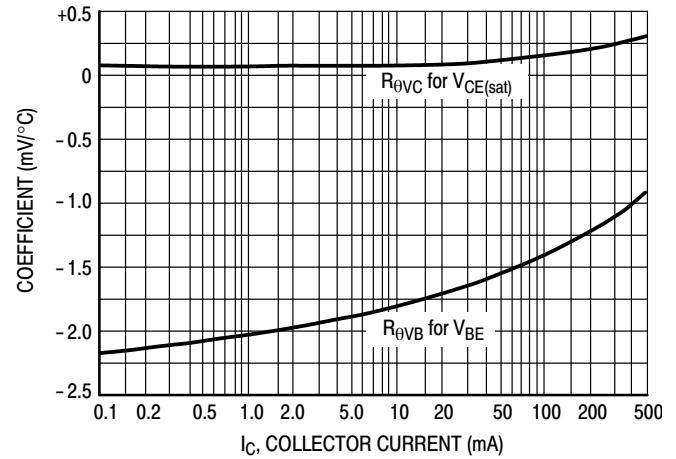
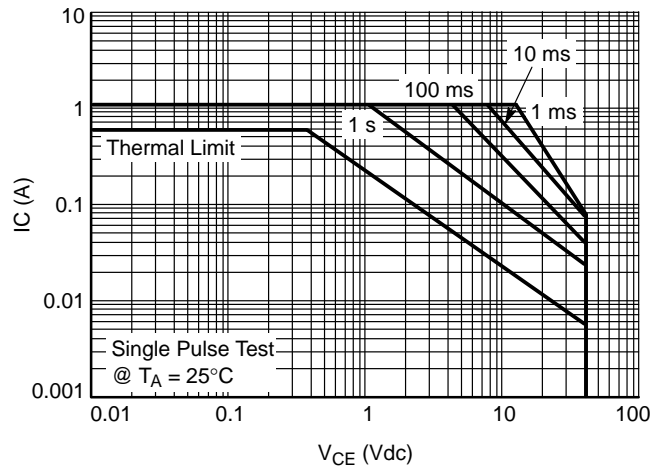


Figure 14. Temperature Coefficients

# MMBT2222L, MMBT2222AL, SMMBT2222AL



**Figure 15. Safe Operating Area**

## ORDERING INFORMATION

Device	Specific Marking Code	Package	Shipping†
MMBT2222LT1G	M1B	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT2222ALT1G, SMMBT2222ALT1G	1P	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT2222LT3G	M1B	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT2222ALT3G, SMMBT2222ALT3G	1P	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

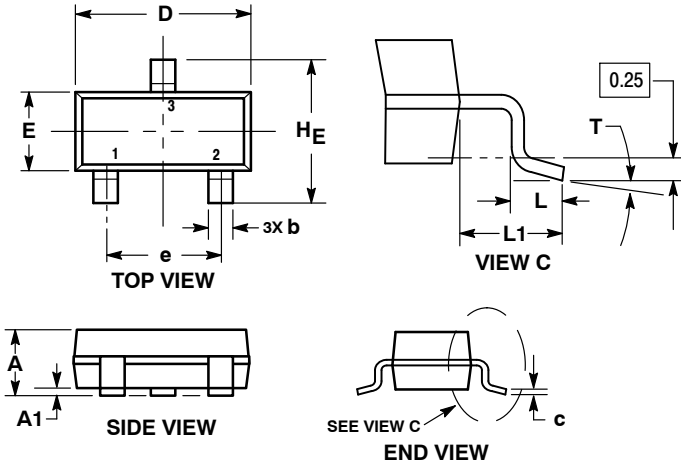
ON Semiconductor®



**SOT-23 (TO-236)**  
CASE 318-08  
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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